

# 2SD2209

## Silicon NPN triple diffusion planar type Darlington

For power amplification and switching

### Features

- I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings (T<sub>C</sub>=25°C)

| Parameter                    | Symbol           | Ratings     | Unit |
|------------------------------|------------------|-------------|------|
| Collector to base voltage    | V <sub>CBO</sub> | 100±15      | V    |
| Collector to emitter voltage | V <sub>CEO</sub> | 100±15      | V    |
| Emitter to base voltage      | V <sub>EBO</sub> | 5           | V    |
| Peak collector current       | I <sub>CP</sub>  | 8           | A    |
| Collector current            | I <sub>C</sub>   | 4           | A    |
| Collector power dissipation  | P <sub>C</sub>   | 15          | W    |
|                              |                  | 1.3         |      |
| Junction temperature         | T <sub>j</sub>   | 150         | °C   |
| Storage temperature          | T <sub>stg</sub> | -55 to +150 | °C   |

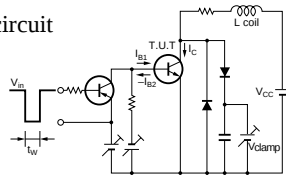
### Electrical Characteristics (T<sub>C</sub>=25°C)

| Parameter                               | Symbol                         | Conditions                                                                                  | min  | typ | max   | Unit |
|-----------------------------------------|--------------------------------|---------------------------------------------------------------------------------------------|------|-----|-------|------|
| Collector cutoff current                | I <sub>CBO</sub>               | V <sub>CB</sub> = 85V, I <sub>E</sub> = 0                                                   |      |     | 100   | μA   |
| Emitter cutoff current                  | I <sub>EBO</sub>               | V <sub>EB</sub> = 5V, I <sub>C</sub> = 0                                                    |      |     | 2     | mA   |
| Collector to emitter voltage            | V <sub>CEO</sub>               | I <sub>C</sub> = 5mA, I <sub>B</sub> = 0                                                    | 85   |     | 115   | V    |
| Forward current transfer ratio          | h <sub>FE1</sub>               | V <sub>CE</sub> = 3V, I <sub>C</sub> = 0.5A                                                 | 1000 |     |       |      |
|                                         | h <sub>FE2</sub> <sup>*1</sup> | V <sub>CE</sub> = 3V, I <sub>C</sub> = 3A                                                   | 1000 |     | 10000 |      |
| Collector to emitter saturation voltage | V <sub>CE(sat)</sub>           | I <sub>C</sub> = 3A, I <sub>B</sub> = 12mA                                                  |      |     | 2     | V    |
|                                         |                                | I <sub>C</sub> = 5A, I <sub>B</sub> = 20mA                                                  |      |     | 4     |      |
| Base to emitter saturation voltage      | V <sub>BE(sat)</sub>           | I <sub>C</sub> = 3A, I <sub>B</sub> = 12mA                                                  |      |     | 2.5   | V    |
| Transition frequency                    | f <sub>T</sub>                 | V <sub>CE</sub> = 10V, I <sub>C</sub> = 0.5A, f = 1MHz                                      |      | 20  |       | MHz  |
| Turn-on time                            | t <sub>on</sub>                | I <sub>C</sub> = 3A, I <sub>B1</sub> = 12mA, I <sub>B2</sub> = -12mA, V <sub>CC</sub> = 50V |      |     | 0.3   | μs   |
| Storage time                            | t <sub>stg</sub>               |                                                                                             |      |     | 3.0   | μs   |
| Fall time                               | t <sub>f</sub>                 |                                                                                             |      |     | 1.0   | μs   |
| Energy handling capability              | E <sub>s/b</sub> <sup>*2</sup> | I <sub>C</sub> = 1A, L = 100mH, R <sub>BE</sub> = 100Ω                                      |      | 50  |       | mJ   |

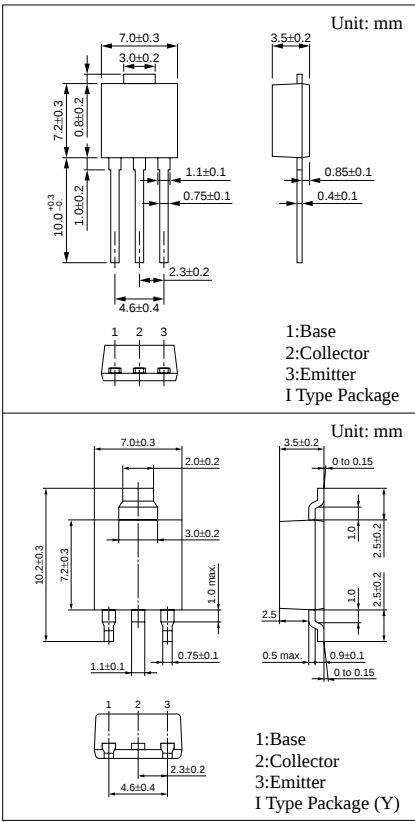
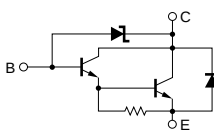
<sup>\*1</sup>h<sub>FE2</sub> Rank classification

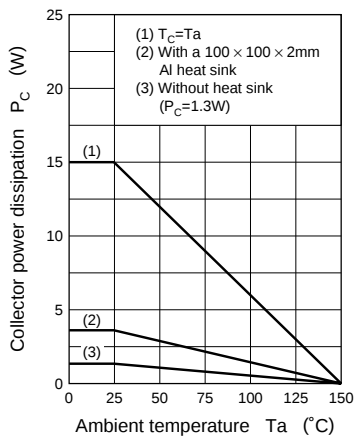
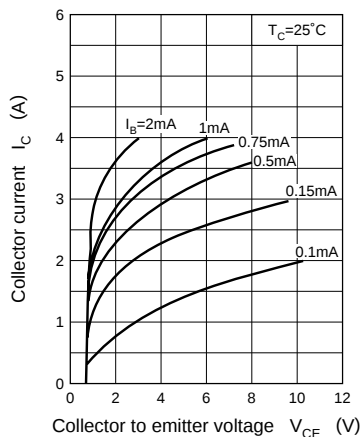
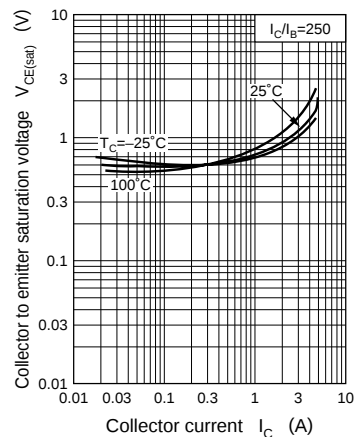
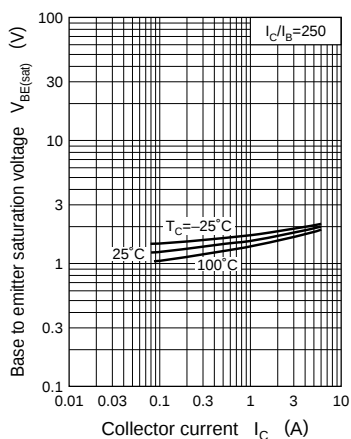
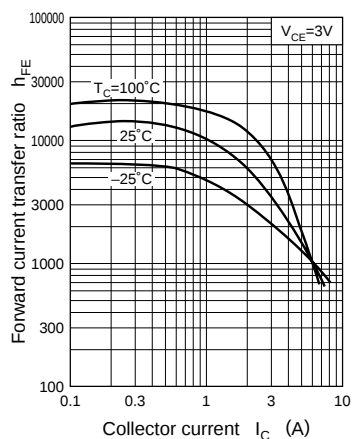
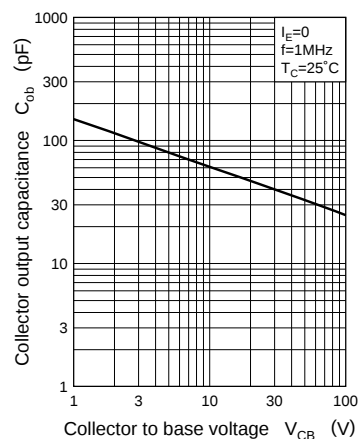
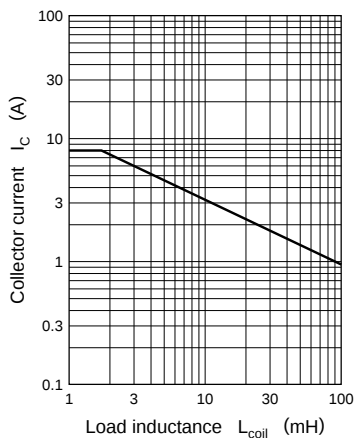
| Rank             | Q            | P             |
|------------------|--------------|---------------|
| h <sub>FE2</sub> | 1000 to 5000 | 2000 to 10000 |

<sup>\*2</sup>E<sub>s/b</sub> Test circuit



Internal Connection



$P_C - T_a$  $I_C - V_{CE}$  $V_{CE(sat)} - I_C$  $V_{BE(sat)} - I_C$  $h_{FE} - I_C$  $C_{ob} - V_{CB}$  $I_C - L_{coil}$ 

Area of safe operation (ASO)

